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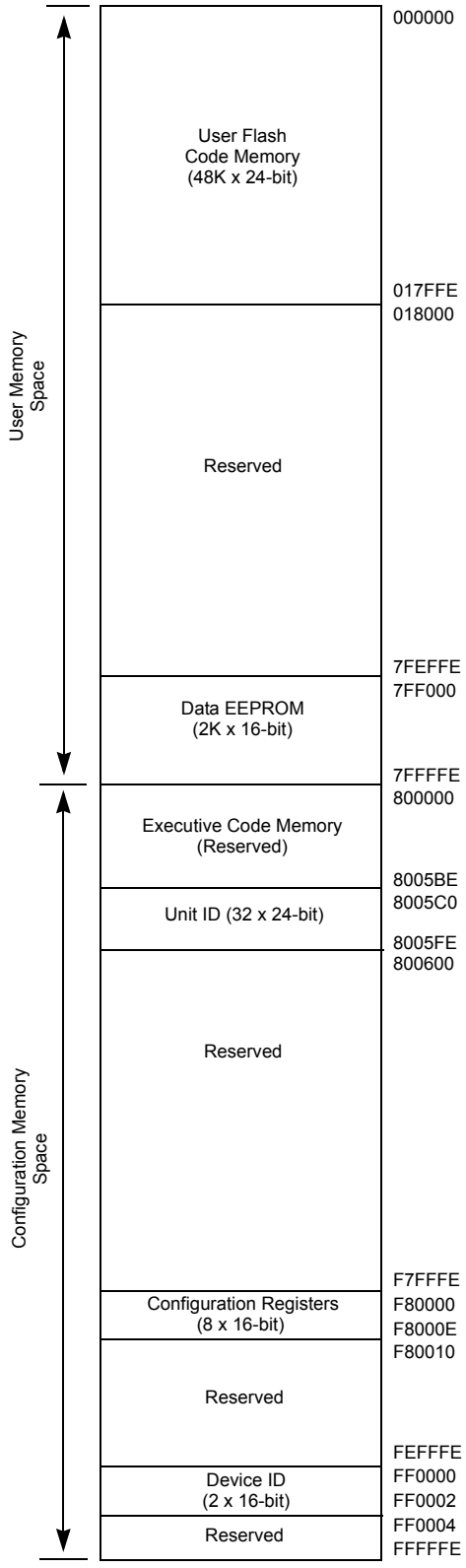
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	30 MIPs
Connectivity	CANbus, I²C, SPI, UART/USART
Peripherals	AC'97, Brown-out Detect/Reset, I²S, LVD, POR, PWM, WDT
Number of I/O	68
Program Memory Size	66KB (22K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-TQFP
Supplier Device Package	80-TQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/dspic30f5013t-30i-ptg

FIGURE 2-2: PROGRAM MEMORY MAP

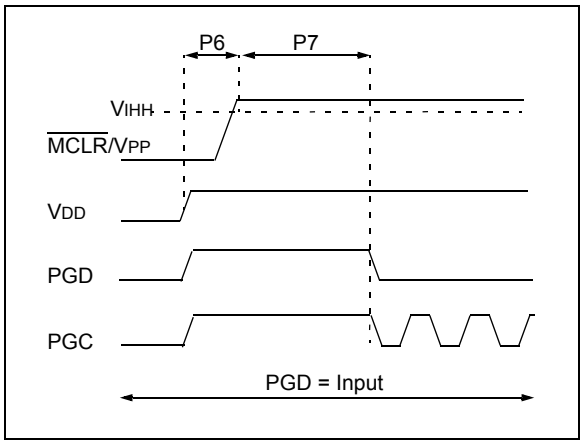


Note: The address boundaries for user Flash code memory and data EEPROM are device-dependent.

5.2 Entering Enhanced ICSP Mode

The Enhanced ICSP mode is entered by holding PGC and PGD high, and then raising MCLR/VPP to VIHH (high voltage), as illustrated in Figure 5-2. In this mode, the code memory, data EEPROM and Configuration bits can be efficiently programmed using the programming executive commands that are serially transferred using PGC and PGD.

FIGURE 5-2: ENTERING ENHANCED ICSP™ MODE



Note 1: The sequence that places the device into Enhanced ICSP mode places all unused I/Os in the high-impedance state.

2: Before entering Enhanced ICSP mode, clock switching must be disabled using ICSP, by programming the FCKSM<1:0> bits in the FOSC Configuration register to '11' or '10'.

3: When in Enhanced ICSP mode, the SPI output pin (SDO1) will toggle while the device is being programmed.

5.3 Chip Erase

Before a chip can be programmed, it must be erased. The Bulk Erase command (ERASEB) is used to perform this task. Executing this command with the MS command field set to 0x3 erases all code memory, data EEPROM and code-protect Configuration bits. The Chip Erase process sets all bits in these three memory regions to '1'.

Since non-code-protect Configuration bits cannot be erased, they must be manually set to '1' using multiple PROGC commands. One PROGC command must be sent for each Configuration register (see **Section 5.7 "Configuration Bits Programming"**).

If Advanced Security features are enabled, then individual Segment Erase operations would need to be performed, depending on which segment needs to be programmed at a given stage of system programming. The user should have the flexibility to select specific segments for programming.

Note: The Device ID registers cannot be erased. These registers remain intact after a Chip Erase is performed.

5.4 Blank Check

The term "Blank Check" means to verify that the device has been successfully erased and has no programmed memory cells. A blank or erased memory cell reads as '1'. The following memories must be blank checked:

- All implemented code memory
- All implemented data EEPROM
- All Configuration bits (for their default value)

The Device ID registers (0xFF0000:0xFF0002) can be ignored by the Blank Check since this region stores device information that cannot be erased. Additionally, all unimplemented memory space should be ignored from the Blank Check.

The QBLANK command is used for the Blank Check. It determines if the code memory and data EEPROM are erased by testing these memory regions. A 'BLANK' or 'NOT BLANK' response is returned. The READD command is used to read the Configuration registers. If it is determined that the device is not blank, it must be erased (see **Section 5.3 "Chip Erase"**) before attempting to program the chip.

5.5 Code Memory Programming

5.5.1 OVERVIEW

The Flash code memory array consists of 512 rows of thirty-two, 24-bit instructions. Each panel stores 16K instruction words, and each dsPIC30F device has either 1, 2 or 3 memory panels (see Table 5-2).

TABLE 5-2: DEVICE CODE MEMORY SIZE

Device	Code Size (24-bit Words)	Number of Rows	Number of Panels
dsPIC30F2010	4K	128	1
dsPIC30F2011	4K	128	1
dsPIC30F2012	4K	128	1
dsPIC30F3010	8K	256	1
dsPIC30F3011	8K	256	1
dsPIC30F3012	8K	256	1
dsPIC30F3013	8K	256	1
dsPIC30F3014	8K	256	1
dsPIC30F4011	16K	512	1
dsPIC30F4012	16K	512	1
dsPIC30F4013	16K	512	1
dsPIC30F5011	22K	704	2
dsPIC30F5013	22K	704	2
dsPIC30F5015	22K	704	2
dsPIC30F5016	22K	704	2
dsPIC30F6010	48K	1536	3
dsPIC30F6010A	48K	1536	3
dsPIC30F6011	44K	1408	3
dsPIC30F6011A	44K	1408	3
dsPIC30F6012	48K	1536	3
dsPIC30F6012A	48K	1536	3
dsPIC30F6013	44K	1408	3
dsPIC30F6013A	44K	1408	3
dsPIC30F6014	48K	1536	3
dsPIC30F6014A	48K	1536	3
dsPIC30F6015	48K	1536	3

5.5.2 PROGRAMMING METHODOLOGY

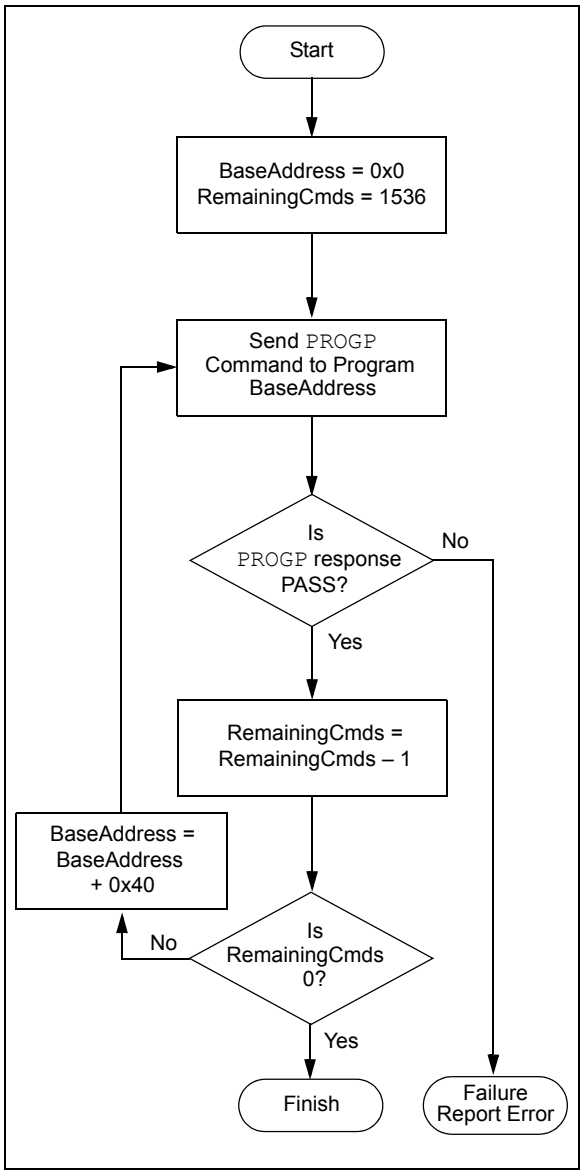
Code memory is programmed with the PROGP command. PROGP programs one row of code memory to the memory address specified in the command. The number of PROGP commands required to program a device depends on the number of rows that must be programmed in the device.

A flowchart for programming of code memory is illustrated in Figure 5-3. In this example, all 48K instruction words of a dsPIC30F6014A device are programmed. First, the number of commands to send (called 'RemainingCmds' in the flowchart) is set to 1536 and the destination address (called 'BaseAddress') is set to '0'.

Next, one row in the device is programmed with a PROGP command. Each PROGP command contains data for one row of code memory of the dsPIC30F6014A. After the first command is processed successfully, 'RemainingCmds' is decremented by 1 and compared to 0. Since there are more PROGP commands to send, 'BaseAddress' is incremented by 0x40 to point to the next row of memory.

On the second PROGP command, the second row of each memory panel is programmed. This process is repeated until the entire device is programmed. No special handling must be performed when a panel boundary is crossed.

FIGURE 5-3: FLOWCHART FOR PROGRAMMING dsPIC30F6014A CODE MEMORY



5.5.3 PROGRAMMING VERIFICATION

Once code memory is programmed, the contents of memory can be verified to ensure that programming was successful. Verification requires code memory to be read back and compared against the copy held in the programmer's buffer.

The `READP` command can be used to read back all the programmed code memory.

Alternatively, you can have the programmer perform the verification once the entire device is programmed using a checksum computation, as described in **Section 6.8 "Checksum Computation"**.

5.6 Data EEPROM Programming

5.6.1 OVERVIEW

The panel architecture for the data EEPROM memory array consists of 128 rows of sixteen 16-bit data words. Each panel stores 2K words. All devices have either one or no memory panels. Devices with data EEPROM provide either 512 words, 1024 words or 2048 words of memory on the one panel (see Table 5-3).

TABLE 5-3: DATA EEPROM SIZE

Device	Data EEPROM Size (Words)	Number of Rows
dsPIC30F2010	512	32
dsPIC30F2011	0	0
dsPIC30F2012	0	0
dsPIC30F3010	512	32
dsPIC30F3011	512	32
dsPIC30F3012	512	32
dsPIC30F3013	512	32
dsPIC30F3014	512	32
dsPIC30F4011	512	32
dsPIC30F4012	512	32
dsPIC30F4013	512	32
dsPIC30F5011	512	32
dsPIC30F5013	512	32
dsPIC30F5015	512	32
dsPIC30F5016	512	32
dsPIC30F6010	2048	128
dsPIC30F6010A	2048	128
dsPIC30F6011	1024	64
dsPIC30F6011A	1024	64
dsPIC30F6012	2048	128
dsPIC30F6012A	2048	128
dsPIC30F6013	1024	64
dsPIC30F6013A	1024	64
dsPIC30F6014	2048	128
dsPIC30F6014A	2048	128
dsPIC30F6015	2048	128

5.6.2 PROGRAMMING METHODOLOGY

The programming executive uses the `PROGD` command to program the data EEPROM. Figure 5-4 illustrates the flowchart of the process. Firstly, the number of rows to program (RemainingRows) is based on the device size, and the destination address (DestAddress) is set to '0'. In this example, 128 rows (2048 words) of data EEPROM will be programmed.

The first `PROGD` command programs the first row of data EEPROM. Once the command completes successfully, 'RemainingRows' is decremented by 1 and compared with 0. Since there are 127 more rows to program, 'BaseAddress' is incremented by 0x20 to point to the next row of data EEPROM. This process is then repeated until all 128 rows of data EEPROM are programmed.

FIGURE 5-4: FLOWCHART FOR PROGRAMMING dsPIC30F6014A DATA EEPROM

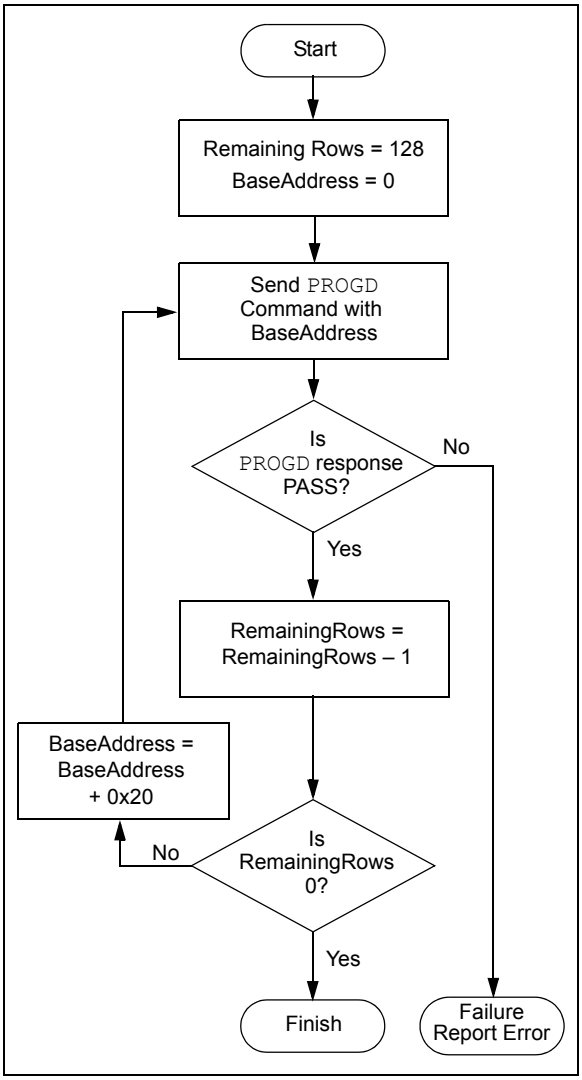


TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015

Bit Field	Register	Description
FCKSM<1:0>	FOSC	**Clock Switching Mode** 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<2:0>	FOSC	**Oscillator Source Selection on POR** 111 = Primary Oscillator 110 = Reserved 101 = Reserved 100 = Reserved 011 = Reserved 010 = Internal Low-Power RC Oscillator 001 = Internal Fast RC Oscillator (no PLL) 000 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<4:0>	FOSC	**Primary Oscillator Mode (when FOS<2:0> = 111b)** 11xxx = Reserved (do not use) 10111 = HS/3 w/PLL 16X – HS/3 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10110 = HS/3 w/PLL 8X – HS/3 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10101 = HS/3 w/PLL 4X – HS/3 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10100 = Reserved (do not use) 10011 = HS/2 w/PLL 16X – HS/2 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10010 = HS/2 w/PLL 8X – HS/2 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal 10001 = HS/2 w/PLL 4X – HS/2 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10000 = Reserved (do not use) 01111 = ECIO w/PLL 16x – External clock with 16x PLL. OSC2 pin is I/O 01110 = ECIO w/PLL 8x – External clock with 8x PLL. OSC2 pin is I/O 01101 = ECIO w/PLL 4x – External clock with 4x PLL. OSC2 pin is I/O 01100 = Reserved (do not use) 01011 = Reserved (do not use) 01010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 01001 = Reserved (do not use) 01000 = Reserved (do not use) 00111 = XT w/PLL 16X – XT crystal oscillator with 16X PLL 00110 = XT w/PLL 8X – XT crystal oscillator with 8X PLL 00101 = XT w/PLL 4X – XT crystal oscillator with 4X PLL 00100 = Reserved (do not use) 00011 = FRC w/PLL 16x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 00010 = Reserved (do not use) 00001 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 00000 = Reserved (do not use)

TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

Bit Field	Register	Description
EBS	FBS	**Boot Segment Data EEPROM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 1 = No Data EEPROM is reserved for Boot Segment 0 = 128 bytes of Data EEPROM are reserved for Boot Segment in dsPIC30F5011/5013, and 256 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015
BSS<2:0>	FBS	**Boot Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 111 = No Boot Segment 110 = Standard security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 101 = Standard security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x000FFF] 100 = Standard security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x001FF] 011 = No Boot Segment 010 = High security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 001 = High security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x000FFF] 000 = High security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x001FFF]
BWRP	FBS	**Boot Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 1 = Boot Segment program memory is not write-protected 0 = Boot Segment program memory is write-protected
RSS<1:0>	FSS	**Secure Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 11 = No Data RAM is reserved for Secure Segment 10 = Small-sized Secure RAM [(256 – N) bytes of RAM are reserved for Secure Segment] 01 = Medium-sized Secure RAM [(768 – N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/5013, and (2048 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 00 = Large-sized Secure RAM [(1024 – N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/5013, and (4096 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] where N = Number of bytes of RAM reserved for Boot Sector.
ESS<1:0>	FSS	**Secure Segment Data EEPROM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 11 = No Data EEPROM is reserved for Secure Segment 10 = Small-sized Secure Data EEPROM [(128 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (256 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 01 = Medium-sized Secure Data EEPROM [(256 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (512 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 00 = Large-sized Secure Data EEPROM [(512 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, (1024 – N) bytes in dsPIC30F6011A/6013A, and (2048 – N) bytes in dsPIC30F6010A/6012A/6014A/6015] where N = Number of bytes of Data EEPROM reserved for Boot Sector.

TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

Bit Field	Register	Description
SSS<2:0>	FSS	**Secure Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 111 = No Secure Segment 110 = Standard security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 101 = Standard security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 100 = Standard security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF] 011 = No Secure Segment 010 = High security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 000 = High security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF]
SWRP	FSS	**Secure Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 1 = Secure Segment program memory is not write-protected 0 = Secure program memory is write-protected
GSS<1:0>	FGS	**General Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 11 = Code protection is disabled 10 = Standard security code protection is enabled 0x = High security code protection is enabled
GCP	FGS	**General Segment Program Memory Code Protection (present in all devices except dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 1 = General Segment program memory is not code-protected 0 = General Segment program memory is code-protected
GWRP	FGS	**General Segment Program Memory Write Protection** 1 = General Segment program memory is not write-protected 0 = General Segment program memory is write-protected
BKBUG	FICD	**Debugger/Emulator Enable** 1 = Device will reset into Operational mode 0 = Device will reset into Debug/Emulation mode
COE	FICD	**Debugger/Emulator Enable** 1 = Device will reset into Operational mode 0 = Device will reset into Clip-on Emulation mode
ICS<1:0>	FICD	**ICD Communication Channel Select** 11 = Communicate on PGC/EMUC and PGD/EMUD 10 = Communicate on EMUC1 and EMUD1 01 = Communicate on EMUC2 and EMUD2 00 = Communicate on EMUC3 and EMUD3
RESERVED	FBS, FSS, FGS	**Reserved (read as '1', write as '1')**
—	All	**Unimplemented (read as '0', write as '0')**

clocked out. The programmer can begin to clock out the response 20 µsec after PGD is brought low, and it must provide the necessary amount of clock pulses to receive the entire response from the programming executive.

Once the entire response is clocked out, the programmer should terminate the clock on PGC until it is time to send another command to the programming executive. This protocol is illustrated in Figure 7-2.

7.3 SPI Rate

In Enhanced ICSP mode, the dsPIC30F operates from the fast internal RC oscillator, which has a nominal frequency of 7.37 MHz. This oscillator frequency yields an effective system clock frequency of 1.84 MHz. Since the SPI module operates in Slave mode, the programmer must limit the SPI clock rate to a frequency no greater than 1 MHz.

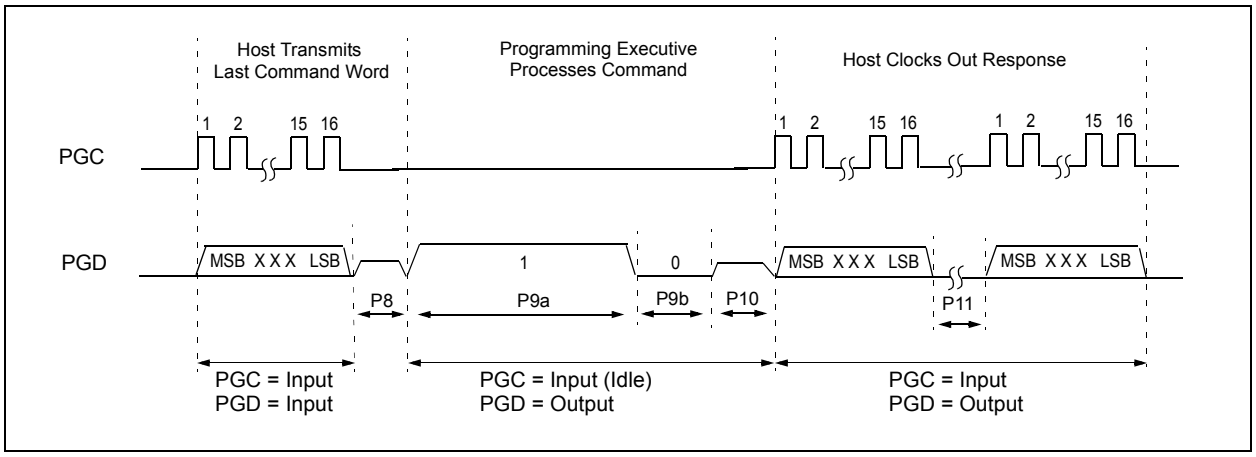
Note:	If the programmer provides the SPI with a clock faster than 1 MHz, the behavior of the programming executive will be unpredictable.

7.4 Time Outs

The programming executive uses no Watchdog Timer or time out for transmitting responses to the programmer. If the programmer does not follow the flow control mechanism using PGC, as described in **Section 7.2 "Communication Interface and Protocol"**, it is possible that the programming executive will behave unexpectedly while trying to send a response to the programmer. Since the programming executive has no time out, it is imperative that the programmer correctly follow the described communication protocol.

As a safety measure, the programmer should use the command time outs identified in Table 8-1. If the command time out expires, the programmer should reset the programming executive and start programming the device again.

FIGURE 7-2: PROGRAMMING EXECUTIVE – PROGRAMMER COMMUNICATION PROTOCOL



8.5.7 ERASEB COMMAND

15 12	11 2	0
Opcode	Length	
Reserved		MS

Field	Description
Opcode	0x7
Length	0x2
Reserved	0x0
MS	Select memory to erase: 0x0 = All Code in General Segment 0x1 = All Data EEPROM in General Segment 0x2 = All Code and Data EEPROM in General Segment, interrupt vectors and FGS Configuration register 0x3 = Full Chip Erase 0x4 = All Code and Data EEPROM in Boot, Secure and General Segments, and FBS, FSS and FGS Configuration registers 0x5 = All Code and Data EEPROM in Secure and General Segments, and FSS and FGS Configuration registers 0x6 = All Data EEPROM in Boot Segment 0x7 = All Data EEPROM in Secure Segment

The ERASEB command performs a Bulk Erase. The MS field selects the memory to be bulk erased, with options for erasing Code and/or Data EEPROM in individual memory segments.

When Full Chip Erase is selected, the following memory regions are erased:

- All code memory (even if code-protected)
- All data EEPROM
- All code-protect Configuration registers

Only the executive code memory, Unit ID, device ID and Configuration registers that are not code-protected remain intact after a Chip Erase.

Expected Response (2 words):
0x1700
0x0002

Note:	A Full Chip Erase cannot be performed in low-voltage programming systems (V_{DD} less than 4.5 volts). ERASED and ERASEP must be used to erase code memory, executive memory and data memory. Alternatively, individual Segment Erase operations may be performed.

8.5.8 ERASED COMMAND

15 12	11 8	7 0
Opcode	Length	
Num_Rows		Addr_MSB
Addr_LS		

Field	Description
Opcode	0x8
Length	0x3
Num_Rows	Number of rows to erase (max of 128)
Addr_MSB	MSB of 24-bit base address
Addr_LS	LS 16 bits of 24-bit base address

The ERASED command erases the specified number of rows of data EEPROM from the specified base address. The specified base address must be a multiple of 0x20. Since the data EEPROM is mapped to program space, a 24-bit base address must be specified.

After the erase is performed, all targeted bytes of data EEPROM will contain 0xFF.

Expected Response (2 words):
0x1800
0x0002

Note:	The ERASED command cannot be used to erase the Configuration registers or device ID. Code-protect Configuration registers can only be erased with the ERASEB command, while the device ID is read-only.

Table 11-4 shows the ICSP programming process for bulk-erasing program memory. This process includes the ICSP command code, which must be transmitted (for each instruction) to the Least Significant bit first using the PGC and PGD pins (see Figure 11-2).

If an individual Segment Erase operation is required, the NVMCON value must be replaced by the value for the corresponding Segment Erase operation.

Note:	Program memory must be erased before writing any data to program memory.

TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS)

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000 0000 0000	040100 040100 000000	GOTO 0x100 GOTO 0x100 NOP
Step 2: Set NVMCON to program the FBS Configuration register.(1)		
0000 0000	24008A 883B0A	MOV #0x4008, W10 MOV W10, NVMCON
Step 3: Initialize the TBLPAG and write pointer (W7) for TBLWT instruction for Configuration register.(1)		

0000
0000
0000
	200F80
	880190
	200067
		MOV #0xF8, W0
		MOV W0, TBLPAG
		MOV #0x6, W7

Step 4: Load the Configuration Register data to W6.(1)		
0000 0000	EB0300 000000	CLR W6 NOP
Step 5: Load the Configuration Register write latch. Advance W7 to point to next Configuration register.(1)		
0000	BB1B86	TBLWTL W6, [W7++]
Step 6: Unlock the NVMCON for programming the Configuration register.(1)		

0000
0000
0000
0000
	200558
	200AA9
	883B38
	883B39
		MOV #0x55, W8
		MOV #0xAA, W9
		MOV W8, NVMKEY
		MOV W9, NVMKEY

Step 7: Initiate the programming cycle.(1)		
0000 0000 0000 – 0000 0000 0000 0000 0000	A8E761 000000 000000 – 000000 000000 A9E761 000000 000000	BSET NVMCON, #WR NOP NOP Externally time 2 ms NOP NOP BCLR NVMCON, #WR NOP NOP
Step 8: Repeat steps 5-7 one time to program 0x0000 to RESERVED2 Configuration register.(1)		
Step 9: Set the NVMCON to erase all Program Memory.		
00000 0000	2407FA 883B0A	MOV #0x407F, W10 MOV W10, NVMCON
Step 10: Unlock the NVMCON for programming.		

Note 1: Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

11.6 Erasing Program Memory in Low-Voltage Systems

The procedure for erasing program memory (all code memory and data memory) in low-voltage systems (with VDD between 2.5 volts and 4.5 volts) is quite different than the procedure for erasing program memory in normal-voltage systems. Instead of using a Bulk Erase operation, each region of memory must be individually erased by row. Namely, all of the code memory, executive memory and data memory must be erased one row at a time. This procedure is detailed in Table 11-5.

Due to security restrictions, the FBS, FSS and FGS register cannot be erased in low-voltage systems. Once any bits in the FGS register are programmed to '0', they can only be set back to '1' by performing a Bulk Erase in a normal-voltage system. Alternatively, a Segment Erase operation can be performed instead of a Bulk Erase.

Normal-voltage systems can also be used to erase program memory as shown in Table 11-5. However, since this method is more time-consuming and does not clear the code-protect bits, it is not recommended.

Note: Program memory must be erased before writing any data to program memory.

TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS)

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize NVMADR and NVMADRU to erase code memory and initialize W7 for row address updates.		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	883B26	MOV W6, NVMADRU
0000	200407	MOV #0x40, W7
Step 3: Set NVMCON to erase 1 row of code memory.		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
Step 4: Unlock the NVMCON to erase 1 row of code memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 5: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
–	–	Externally time 'P13a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP

TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 18: Unlock the NVMCON to erase 1 row of data memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 19: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
–	–	Externally time 'P13a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
Step 20: Update the row address stored in NVMADR.		
0000	430307	ADD W6, W7, W6
0000	883B16	MOV W6, NVMADR
Step 21: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 22: Repeat Steps 17-21 until all rows of data memory are erased.		

11.7 Writing Configuration Memory

The FOSC, FWDT, FBORPOR and FICD registers are not erasable. It is recommended that all Configuration registers be set to a default value after erasing program memory. The FWDT, FBORPOR and FICD registers can be set to a default all '1's value by programming 0xFFFF to each register. Since these registers contain unimplemented bits that read as '0' the default values shown in Table 11-6 will be read instead of 0xFFFF. The recommended default FOSC value is 0xC100, which selects the FRC clock oscillator setting.

The FGS, FBS and FSS Configuration registers are special since they enable code protection for the device. For security purposes, once any bit in these registers is programmed to '0' (to enable some code protection feature), it can only be set back to '1' by performing a Bulk Erase or Segment Erase as described in **Section 11.5 "Erasing Program Memory in Normal-Voltage Systems"**. Programming these bits from a '0' to '1' is not possible, but they may be programmed from a '1' to a '0' to enable code protection.

Table 11-7 shows the ICSP programming details for clearing the Configuration registers. In Step 1, the Reset vector is exited. In Step 2, the write pointer (W7) is loaded with 0x0000, which is the original destination address (in TBLPAG 0xF8 of program memory). In Step 3, the NVMCON is set to program one Configuration register. In Step 4, the TBLPAG register is initialized, to 0xF8, for writing to the Configuration registers. In Step 5, the value to write to the each Configuration register (0xFFFF) is loaded to W6. In Step 6, the Configuration register data is written to the write latch using the TBLWTL instruction. In Steps 7 and 8, the NVMCON is unlocked for programming and the programming cycle is initiated, as described in **Section 11.4 "Flash Memory Programming in ICSP Mode"**. In Step 9, the internal PC is set to 0x100 as a safety measure to prevent the PC from incrementing into unimplemented memory. Lastly, Steps 3-9 are repeated six times until all seven Configuration registers are cleared.

TABLE 11-6: DEFAULT CONFIGURATION REGISTER VALUES

Address	Register	Default Value
0xF80000	FOSC	0xC100
0xF80002	FWDT	0x803F
0xF80004	FBORPOR	0x87B3
0xF80006	FBS	0x310F
0xF80008	FSS	0x330F
0xF8000A	FGS	0x0007
0xF8000C	FICD	0xC003

TABLE 11-7: SERIAL INSTRUCTION EXECUTION FOR WRITING CONFIGURATION REGISTERS

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000 0000 0000	040100 040100 000000	GOTO 0x100 GOTO 0x100 NOP
Step 2: Initialize the write pointer (W7) for the TBLWT instruction.		
0000	200007	MOV #0x0000, W7
Step 3: Set the NVMCON to program 1 Configuration register.		
0000 0000	24008A 883B0A	MOV #0x4008, W10 MOV W10, NVMCON
Step 4: Initialize the TBLPAG register.		
0000 0000	200F80 880190	MOV #0xF8, W0 MOV W0, TBLPAG
Step 5: Load the Configuration register data to W6.		
0000 0000	2xxxx0 000000	MOV #<CONFIG_VALUE>, W0 NOP

11.11 Reading Configuration Memory

The procedure for reading configuration memory is similar to the procedure for reading code memory, except that 16-bit data words are read instead of 24-bit words. Since there are seven Configuration registers, they are read one register at a time.

Table 11-11 shows the ICSP programming details for reading all of the configuration memory. Note that the TBLPAG register is hard-coded to 0xF8 (the upper byte address of configuration memory), and the read pointer W6 is initialized to 0x0000.

TABLE 11-11: SERIAL INSTRUCTION EXECUTION FOR READING ALL CONFIGURATION MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG, and the read pointer (W6) and the write pointer (W7) for TBLRD instruction.		
0000	200F80	MOV #0xF8, W0
0000	880190	MOV W0, TBLPAG
0000	EB0300	CLR W6
0000	EB0380	CLR W7
0000	000000	NOP
Step 3: Read the Configuration register and write it to the VISI register (located at 0x784).		
0000	BA0BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	883C20	MOV W0, VISI
0000	000000	NOP
Step 4: Output the VISI register using the REGOUT command.		
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
Step 5: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 6: Repeat steps 3-5 six times to read all of configuration memory.		

11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 4: Output W0:W5 using the VISI register and REGOUT command.		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
Step 5: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 6: Repeat steps 3-5 until all desired data memory is read.		

12.2 Programming Verification

After the programming executive has been programmed to executive memory using ICSP, it must be verified. Verification is performed by reading out the contents of executive memory and comparing it with the image of the programming executive stored in the programmer.

Reading the contents of executive memory can be performed using the same technique described in **Section 11.10 "Reading Code Memory"**. A procedure for reading executive memory is shown in Table 12-2. Note that in Step 2, the TBLPAG register is set to 0x80 such that executive memory may be read.

TABLE 12-2: READING EXECUTIVE MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	EB0300	CLR W6
Step 3: Initialize the write pointer (W7), and store the next four locations of executive memory to W0:W5.		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [++W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [++W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP

13.0 AC/DC CHARACTERISTICS AND TIMING REQUIREMENTS

TABLE 13-1: AC/DC CHARACTERISTICS

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	**Sym**	**Characteristic**	**Min**	**Max**	**Units**	**Conditions**
D110	VIHH	High Programming Voltage on $\overline{MCLR}$/VPP	9.00	13.25	V	—
D112	IPP	Programming Current on $\overline{MCLR}$/VPP	—	300	μA	—
D113	IDDP	Supply Current during programming	—	30	mA	Row Erase Program memory
			—	30	mA	Row Erase Data EEPROM
			—	30	mA	Bulk Erase
D001	VDD	Supply voltage	2.5	5.5	V	—
D002	VDDBULK	Supply voltage for Bulk Erase programming	4.5	5.5	V	—
D031	VIL	Input Low Voltage	VSS	0.2 VSS	V	—
D041	VIH	Input High Voltage	0.8 VDD	VDD	V	—
D080	VOL	Output Low Voltage	—	0.6	V	IOL = 8.5 mA
D090	VOH	Output High Voltage	VDD - 0.7	—	V	IOH = -3.0 mA
D012	CIO	Capacitive Loading on I/O Pin (PGD)	—	50	pF	To meet AC specifications
P1	TSCLK	Serial Clock (PGC) period	50	—	ns	ICSP™ mode
			1	—	μs	Enhanced ICSP mode
P1a	TSCLKL	Serial Clock (PGC) low time	20	—	ns	ICSP mode
			400	—	ns	Enhanced ICSP mode
P1b	TSCLKH	Serial Clock (PGC) high time	20	—	ns	ICSP mode
			400	—	ns	Enhanced ICSP mode
P2	TSET1	Input Data Setup Timer to PGC ↓	15	—	ns	—
P3	THLD1	Input Data Hold Time from PGC ↓	15	—	ns	—
P4	TDLY1	Delay between 4-bit command and command operand	20	—	ns	—
P4a	TDLY1a	Delay between 4-bit command operand and next 4-bit command	20	—	ns	—
P5	TDLY2	Delay between last PGC ↓of command to first PGC ↑ of VISI output	20	—	ns	—
P6	TSET2	VDD ↑ setup time to $\overline{MCLR}$/VPP	100	—	ns	—
P7	THLD2	Input data hold time from $\overline{MCLR}$/VPP ↑	2	—	μs	ICSP mode
			5	—	ms	Enhanced ICSP mode
P8	TDLY3	Delay between last PGC ↓of command word to PGD driven ↑ by programming executive	20	—	μs	—
P9a	TDLY4	Programming Executive Command processing time	10	—	μs	—

APPENDIX B: HEX FILE FORMAT

Flash programmers process the standard HEX format used by the Microchip development tools. The format supported is the Intel® HEX 32 Format (INHX32). Please refer to Appendix A in the "*MPASM User's Guide"* (DS33014) for more information about hex file formats.

The basic format of the hex file is:

```
:BBAAAATTHHHH...HHHHCC
```

Each data record begins with a 9-character prefix and always ends with a 2-character checksum. All records begin with '`:`' regardless of the format. The individual elements are described below.

- `BB` - is a two-digit hexadecimal byte count representing the number of data bytes that appear on the line. Divide this number by two to get the number of words per line.
- `AAAA` - is a four-digit hexadecimal address representing the starting address of the data record. Format is high byte first followed by low byte. The address is doubled because this format only supports 8-bits. Divide the value by two to find the real device address.
- `TT` - is a two-digit record type that will be '00' for data records, '01' for end-of-file records and '04' for extended-address record.
- `HHHH` - is a four-digit hexadecimal data word. Format is low byte followed by high byte. There will be `BB`/2 data words following `TT`.
- `CC` - is a two-digit hexadecimal checksum that is the two's complement of the sum of all the preceding bytes in the line record.

Because the Intel hex file format is byte-oriented, and the 16-bit program counter is not, program memory sections require special treatment. Each 24-bit program word is extended to 32 bits by inserting a so-called "phantom byte". Each program memory address is multiplied by 2 to yield a byte address.

As an example, a section that is located at 0x100 in program memory will be represented in the hex file as 0x200.

The hex file will be produced with the following contents:

```
:020000040000fa
:040200003322110096
:00000001FF
```

Notice that the data record (line 2) has a load address of 0200, while the source code specified address 0x100. Note also that the data is represented in "little-endian" format, meaning the Least Significant Byte (LSB) appears first. The phantom byte appears last, just before the checksum.

APPENDIX C: REVISION HISTORY

Note: Revision histories were not recorded for revisions A through H. The previous revision (J), was published in August 2007.

Revision K (November 2010)

This version of the document includes the following updates:

- Added Note three to **Section 5.2 "Entering Enhanced ICSP Mode"**
- Updated the first paragraph of **Section 10.0 "Device ID"**
- Updated Table 10-1: Device IDs
- Removed the VARIANT bit and updated the bit definition for the DEVID register in Table 10-2: dsPIC30F Device ID Registers
- Removed the VARIANT bit and updated the bit field definition and description for the DEVID register in Table 10-3: Device ID Bits Description
- Updated Note 3 in **Section 11.3 "Entering ICSP Mode"**
- Updated Step 11 in Table 11-4: Serial Instruction Execution for BUlk Erasing Program Memory (Only in Normal-voltage Systems)
- Updated Steps 5, 12 and 19 in Table 11-5: Serial Instruction Execution for Erasing Program Memory (Either in Low-voltage or Normal-voltage Systems)
- Updated Steps 5, 6 and 8 in Table 11-7: Serial Instruction Execution for Writing Configuration Registers
- Updated Steps 6 and 8 in Table 11-8: Serial Instruction Execution for Writing Code Memory
- Updated Steps 6 and 8 in Table 11-9: Serial Instruction Execution for Writing Data EEPROM
- Updated Entering ICSP™ Mode (see Figure 11-4)
- Updated Steps 4 and 11 in Table 12-1: Programming the Programming Executive
- Renamed parameters: P12 to P12a and P13 to P13a, and added parameters P12b and P13b in Table 13-1: AC/DC Characteristics

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

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Microchip received ISO/TS-16949:2002 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.